



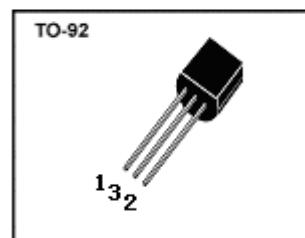
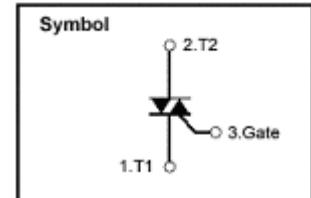
Shantou Huashan Electronic Devices Co.,Ltd.

HTR1A60

BI-DIRECTIONAL TRIODE THYRISTOR (TRIAC)

Features

- * Repetitive Peak Off-State Voltage: 600V
- * R.M.S On-state Current($I_{T(RMS)}=1A$)
- * High Commutation dv/dt



General Description

The Triac HTR1A60 is suitable for AC switching application, phase control application such as heater control, motor control, lighting control, and static switching relay.

Absolute Maximum Ratings ($T_a=25^\circ C$)

T_{stg} ——Storage Temperature	-40~125
T_J ——Operating Junction Temperature	-40~125
P_{GM} ——Peak Gate Power Dissipation	1W
$P_{G(AV)}$ ——Average Gate Power Dissipation	0.1W
V_{DRM} ——Repetitive Peak Off-State Voltage	600V
IT (RMS) ——R.M.S On-State Current ($T_a=58^\circ C$)	1A
V_{GM} ——Peak Gate Voltage	6V
I_{GM} ——Peak Gate Current	0.5A
$ITSM$ ——Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive)	9.1/10A



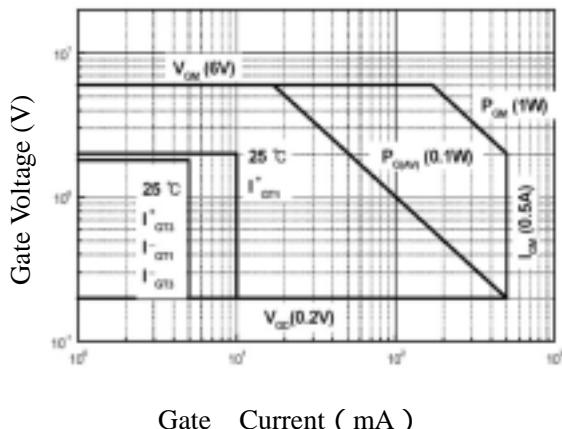
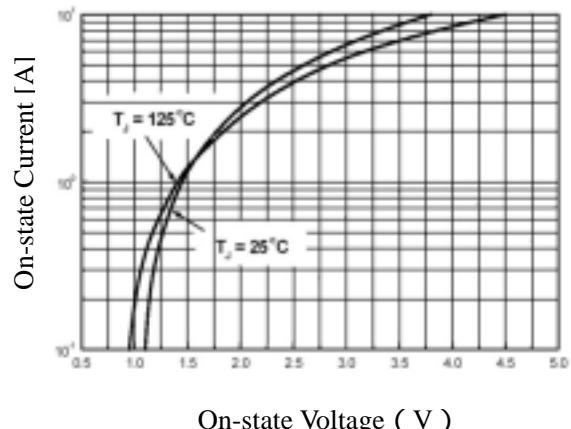
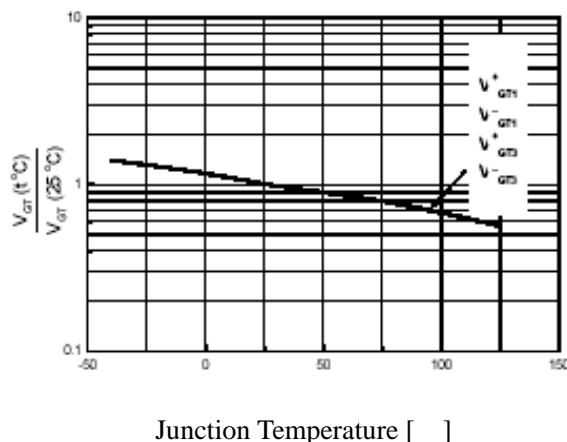
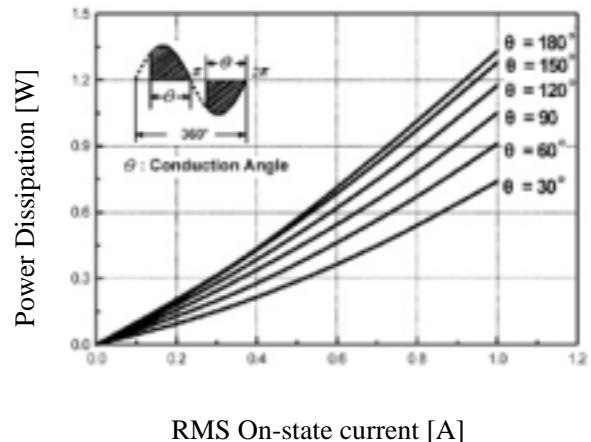
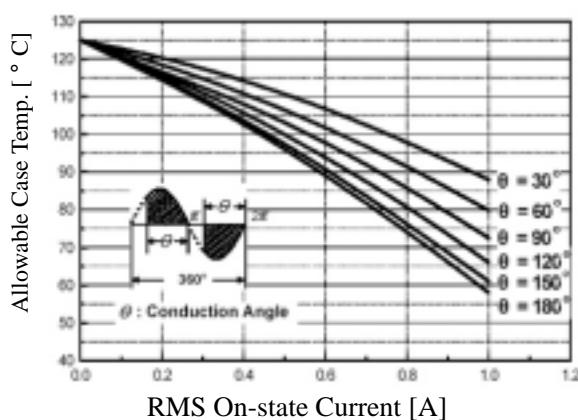
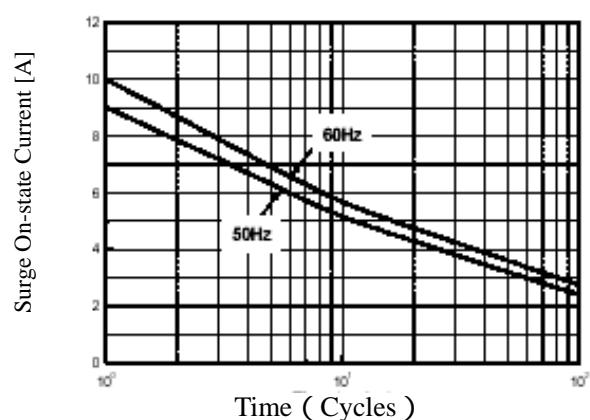
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HTR1A60**Electrical Characteristics (T_a=25)**

Symbol	Items	Min.	Typ.	Max.	Unit	Conditions
I _{DRM}	Repetitive Peak Off-state Current			0.5	mA	V _D =V _{DRM} , Single Phase, Half Wave, T _J =125
V _{TM}	Peak On-State Voltage			1.6	V	I _T =1.5A, Inst. Measurement
I _{+GT1}	Gate Trigger Current (+)			5.0	mA	V _D =6V, R _L =10 ohm
I _{-GT1}	Gate Trigger Current (-)			5.0	mA	V _D =6V, R _L =10 ohm
I _{-GT3}	Gate Trigger Current (-)			5.0	mA	V _D =6V, R _L =10 ohm
I _{+GT3}	Gate Trigger Current (+)			10.0	mA	V _D =6V, R _L =10 ohm
V _{+GT1}	Gate Trigger Voltage (+)			1.8	V	V _D =6V, R _L =10 ohm
V _{-GT1}	Gate Trigger Voltage (-)			1.8	V	V _D =6V, R _L =10 ohm
V _{-GT3}	Gate Trigger Voltage (-)			1.8	V	V _D =6V, R _L =10 ohm
V _{+GT3}	Gate Trigger Voltage (+)			2.0	V	V _D =6V, R _L =10 ohm
V _{GD}	Non-Trigger Gate Voltage	0.2			V	T _J =125 , V _D =1/2V _{DRM}
(dv/dt) _c	Critical Rate of Rise of Off-State Voltage at Commutation	2.0			V/ μ S	T _J =125 , V _D =2/3V _{DRM} (di/dt) _c =-0.5A/ms
I _H	Holding Current		4.0		mA	
R _{th(j-c)}	Thermal Resistance			50	/W	Junction to case
R _{th(j-a)}	Thermal Resistance			120	/W	Junction to Ambient



Performance Curves

Fig 1. Gate Characteristics**Fig 2. On-State Voltage****Fig 3. Gate Trigger Voltage vs. Junction Temperature****Fig 4. On State Current vs. Maximum Power Dissipation****Fig 5. On State Current vs. Allowable Case Temperature****Fig 6. Surge On-State Current Rating (Non-Repetitive)**



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HTR1A60

**Fig 7. Gate Trigger Current vs.
Junction Temperature**

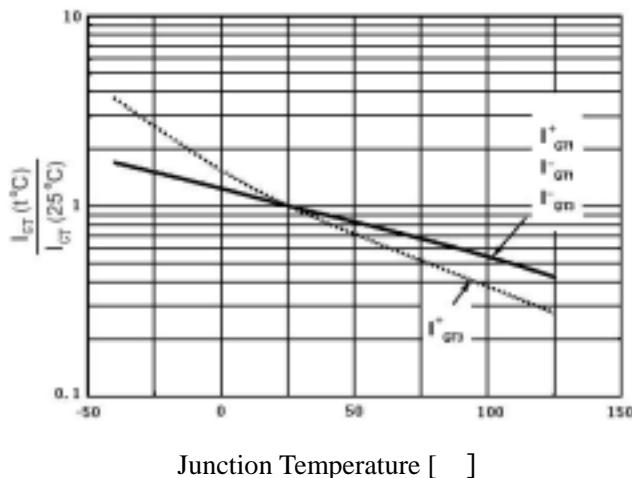


Fig 8. Transient Thermal Impedance

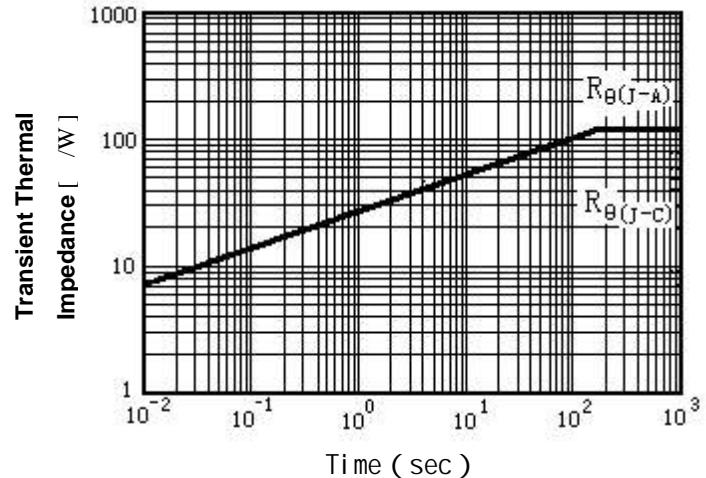
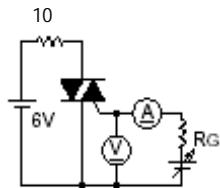
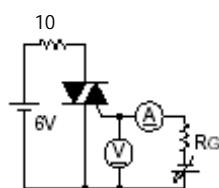


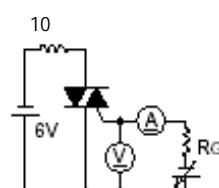
Fig 9. Gate Trigger Characteristics Test Circuit



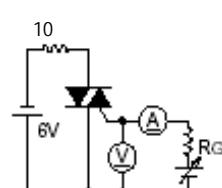
Test Procedure



Test Procedure



Test Procedure



Test Procedure